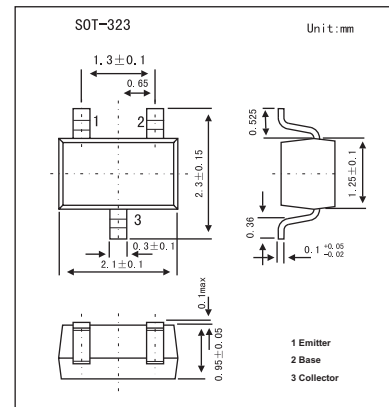


## PNP General Purpose Transistor

## 2PA1576

## ■ Features

- Low current (max. 100 mA)
- Low voltage (max. 40 V).
- Low collector capacitance (typ. 2.5 pF).

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Rating	Unit
Collector-base voltage	$V_{CB0}$	-50	V
Collector-emitter voltage	$V_{CEO}$	-40	V
Emitter-base voltage	$V_{EBO}$	-5	V
Collector current	$I_C$	-100	mA
Peak collector current	$I_{CM}$	-200	mA
Peak base current	$I_{BM}$	-200	mA
Total power dissipation	$P_{tot}$	200	mW
Storage temperature	$T_{stg}$	-65 to +150	$^\circ\text{C}$
Junction temperature	$T_j$	150	$^\circ\text{C}$
Operating ambient temperature	$T_{amb}$	-65 to +150	$^\circ\text{C}$
thermal resistance from junction to ambient	$R_{th\ j-a}$	625	K/W

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cut-off current	$I_{CBO}$	$I_E = 0; V_{CB} = -30\text{ V}$			-100	nA
		$I_E = 0; V_{CB} = -30\text{ V}; T_j = 150\text{ }^\circ\text{C}$			-5	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$I_C = 0; V_{EB} = -4\text{ V}$			-100	nA
DC current gain 2PA1576Q 2PA1576R 2PA1576S	$h_{FE}$	$I_C = -1\text{ mA}; V_{CE} = -6\text{ V}$	120 180 270		270 390 560	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -50\text{ mA}; I_B = -5\text{ mA}; *$			-500	mV
Collector capacitance	$C_c$	$I_E = i_e = 0; V_{CB} = -12\text{ V}; f = 1\text{ MHz}$		2.5	3.5	pF
Transition frequency	$f_T$	$I_C = -2\text{ mA}; V_{CE} = -12\text{ V}; f = 100\text{ MHz}$	100			MHz

\* Pulse test:  $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02$ .

■  $h_{FE}$  Classification

TYPE	2PA1576Q	2PA1576R	2PA1576S
Marking	FQ	FR	FS